



CST2306 N-Ch 30V Fast Switching MOSFETs

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Advanced high cell density Trench technology

CST2306 Product Summary



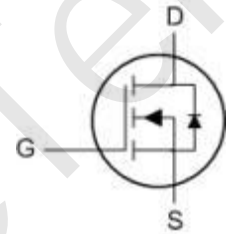
BVDSS	RDSON	ID
30V	29mΩ	4.0A

CST2306 Description

The CST2306 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The CST2306 meet the RoHS and Green Product requirement with full function reliability approved.

CST2306 SOT23 Pin Configuration



CST2306 Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	4.0	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	2.6	A
I _{DM}	Pulsed Drain Current ²	16.4	A
P _D @T _A =25°C	Total Power Dissipation ³	1	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

CST2306 Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	---	125	°C/ W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	80	°C/ W



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CST2306 Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note2	V _{GS} =10V, I _D =4A	-	29	38	mΩ
		V _{GS} =4.5V, I _D =3A	-	45	65	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	233	-	pF
C _{oss}	Output Capacitance		-	44	-	pF
C _{rss}	Reverse Transfer Capacitance		-	33	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =2A, V _{GS} =10V	-	3	-	nC
Q _{gs}	Gate-Source Charge		-	0.5	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	0.8	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, I _D =4A, R _{GEN} =3Ω, V _{GS} =10V	-	4	-	ns
t _r	Turn-on Rise Time		-	2.1	-	ns
t _{d(off)}	Turn-off Delay Time		-	15	-	ns
t _f	Turn-off Fall Time		-	3.2	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	4	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =4A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



CST2306 Typical Performance Characteristics

Figure 1: Output Characteristics

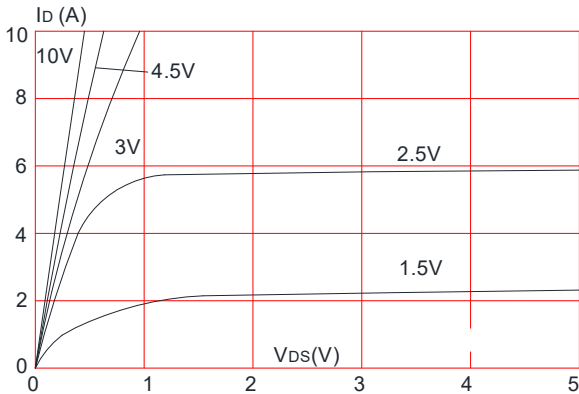


Figure 2: Typical Transfer Characteristics

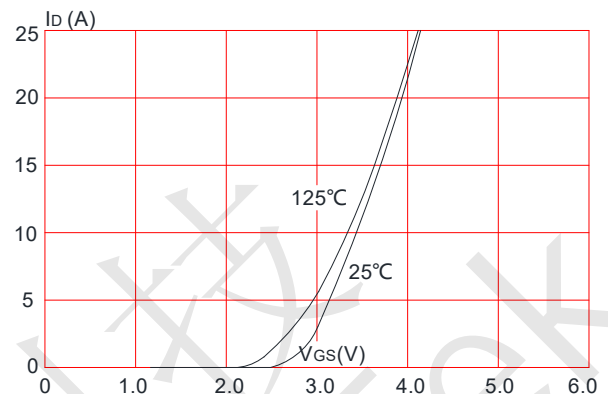


Figure 3: On-resistance vs. Drain Current

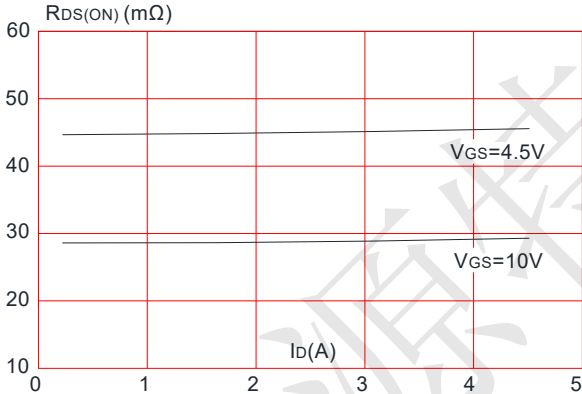


Figure 4: Body Diode Characteristics

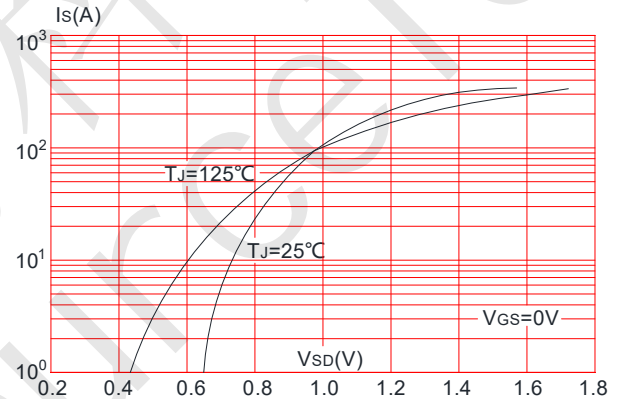


Figure 5: Gate Charge Characteristics

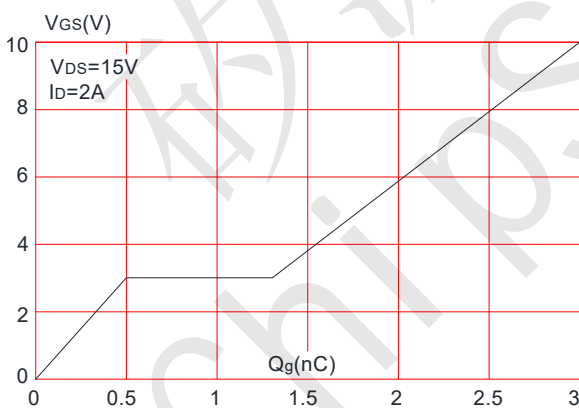
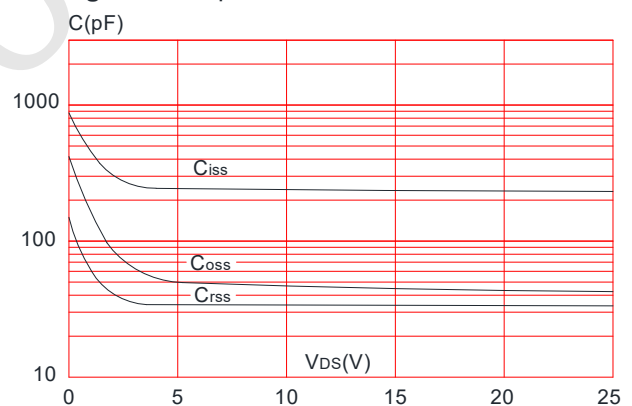


Figure 6: Capacitance Characteristics





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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

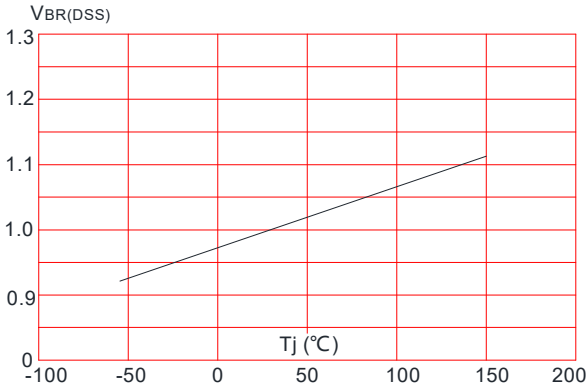


Figure 8: Normalized on Resistance vs. Junction Temperature

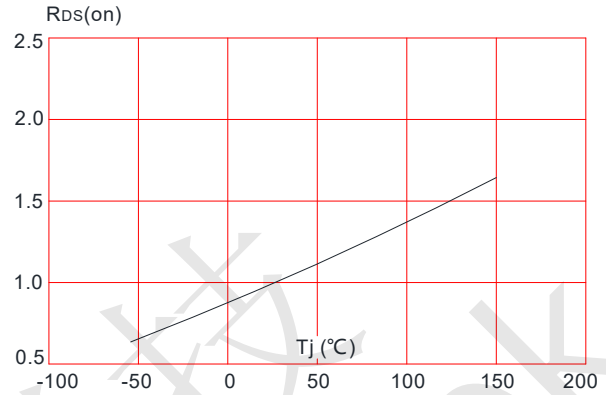


Figure 9: Maximum Safe Operating Area

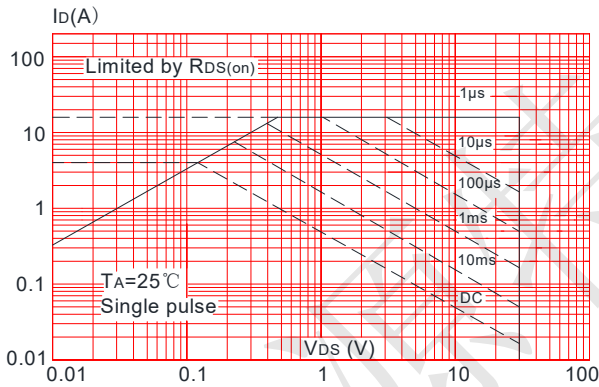


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

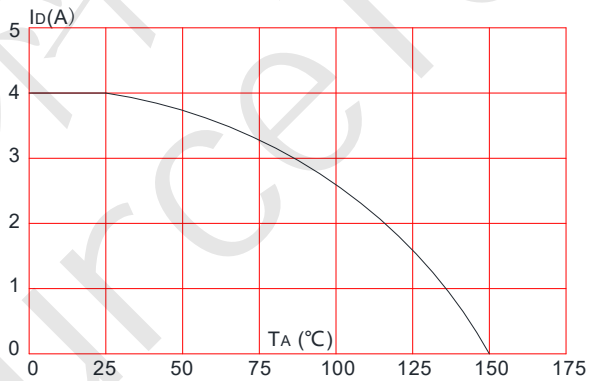
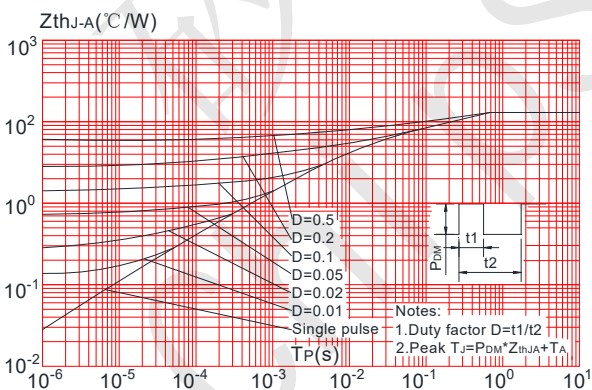


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





CST2306 Test Circuit

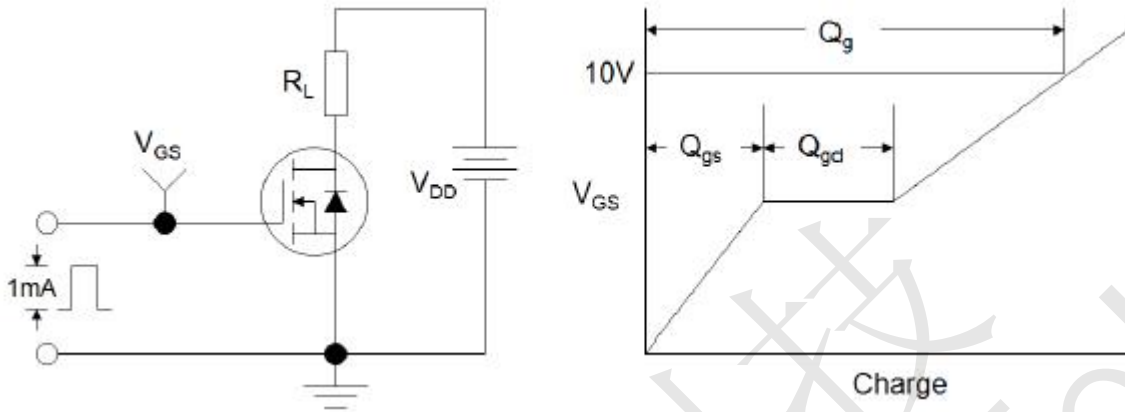


Figure1:Gate Charge Test Circuit & Waveform

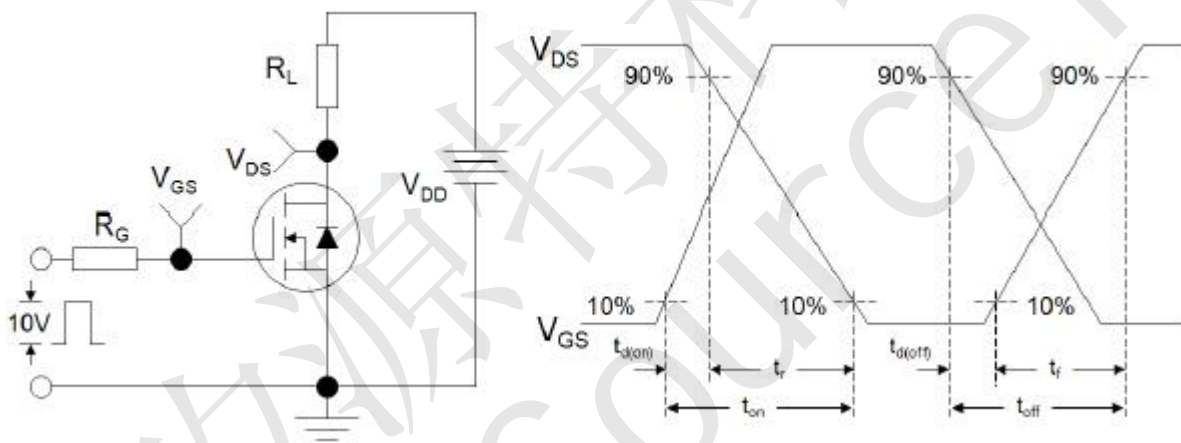


Figure 2: Resistive Switching Test Circuit & Waveforms

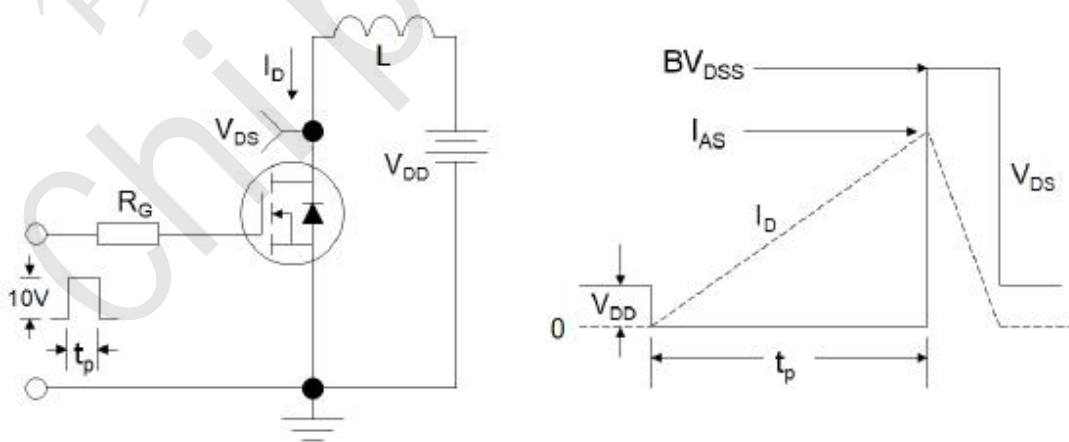
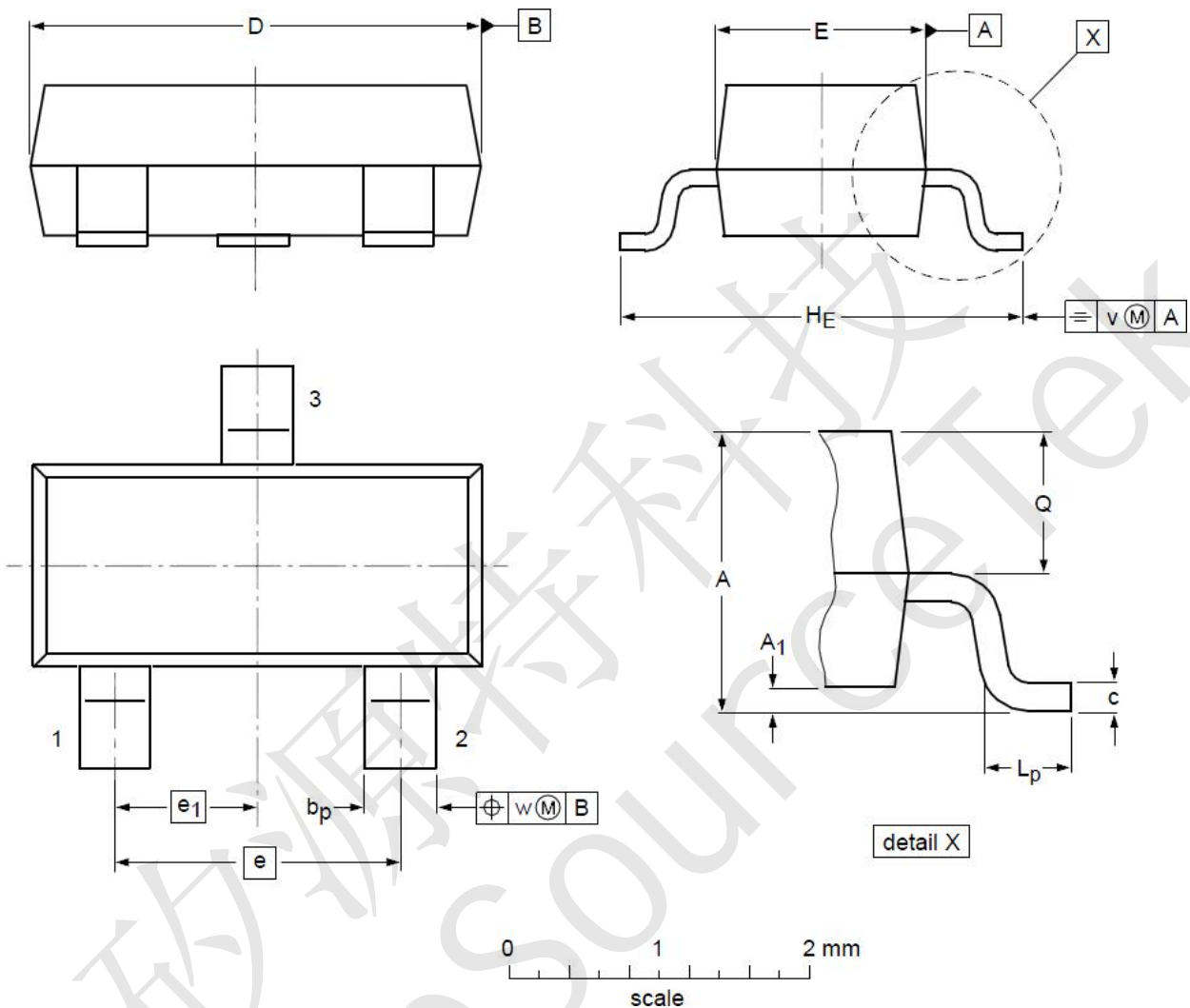


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



CST2306 Package Mechanical Data-SOT-23



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	A ₁	0.01	0.05	0.10
b _p	0.30	0.42	0.50	c	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e ₁	--	0.95	--
H _E	2.25	2.40	2.55	L _p	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				